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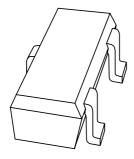
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **1PS181**High-speed double diode

Product data sheet Supersedes data of April 1996 1996 Sep 03



# High-speed double diode

1PS181

#### **FEATURES**

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 80 V
- Repetitive peak reverse voltage: max. 85 V
- Repetitive peak forward current: max. 500 mA.

#### **APPLICATIONS**

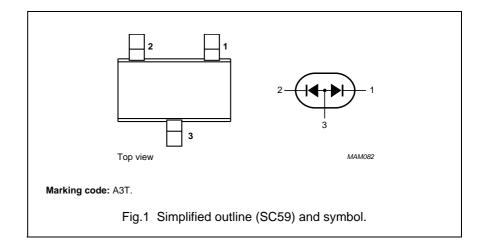
 High-speed switching in e.g. surface mounted circuits.

#### **DESCRIPTION**

The 1PS181 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in the small plastic SMD SC59 package.

#### **PINNING**

PIN	DESCRIPTION
1	cathode (k1)
2	cathode (k2)
3	common anode



#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode	Per diode				
V <sub>RRM</sub>	repetitive peak reverse voltage		_	85	V
$V_R$	continuous reverse voltage		-	80	V
I <sub>F</sub>	continuous forward current	single diode loaded; see Fig.2; note 1	-	215	mA
		double diode loaded; see Fig.2; note 1	_	125	mA
I <sub>FRM</sub>	repetitive peak forward current		_	500	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge			
		t = 1 μs	_	4	Α
		t = 1 s	_	0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C

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#### Note

1. Device mounted on an FR4 printed-circuit board.

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# High-speed double diode

1PS181

#### **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
Per diode					
V <sub>F</sub>	forward voltage	see Fig.3			
		I <sub>F</sub> = 1 mA	610	-	mV
		I <sub>F</sub> = 10 mA	740	_	mV
		I <sub>F</sub> = 50 mA	_	1.0	V
		I <sub>F</sub> = 100 mA	_	1.2	V
I <sub>R</sub>	reverse current	see Fig.4			
		V <sub>R</sub> = 25 V	_	30	nA
		V <sub>R</sub> = 80 V	_	0.5	μΑ
		V <sub>R</sub> = 25 V; T <sub>j</sub> = 150 °C	_	30	μΑ
		V <sub>R</sub> = 80 V; T <sub>j</sub> = 150 °C	_	100	μΑ
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.5	_	2.0	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F$ = 10 mA to $I_R$ = 10 mA; $R_L$ = 100 $\Omega$ ; measured at $I_R$ = 1 mA; see Fig.6	-	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 10$ mA; $t_r = 20$ ns; see Fig.7	-	1.75	V

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point		250	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

#### Note

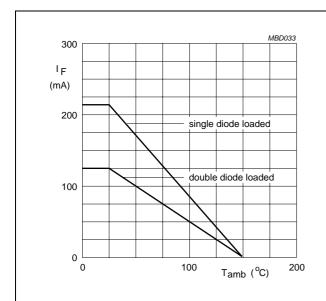
1. Device mounted on an FR4 printed-circuit board.

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# High-speed double diode

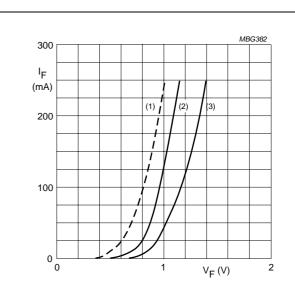
1PS181

#### **GRAPHICAL DATA**



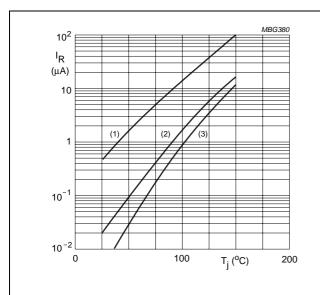
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient temperature.



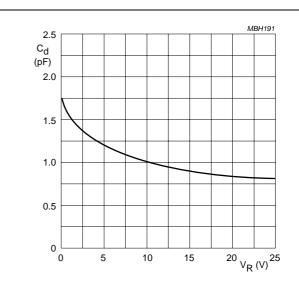
- (1) T<sub>j</sub> = 150 °C; typical values.
- (2)  $T_j = 25$  °C; typical values.
- (3)  $T_j = 25$  °C; maximum values.

Fig.3 Forward current as a function of forward voltage.



- (1)  $V_R = 80 \text{ V}$ ; maximum values.
- (2)  $V_R = 80 \text{ V}$ ; typical values.
- (3)  $V_R = 25 \text{ V}$ ; typical values.

Fig.4 Reverse current as a function of junction temperature.



f = 1 MHz;  $T_j = 25 \,^{\circ}\text{C}$ .

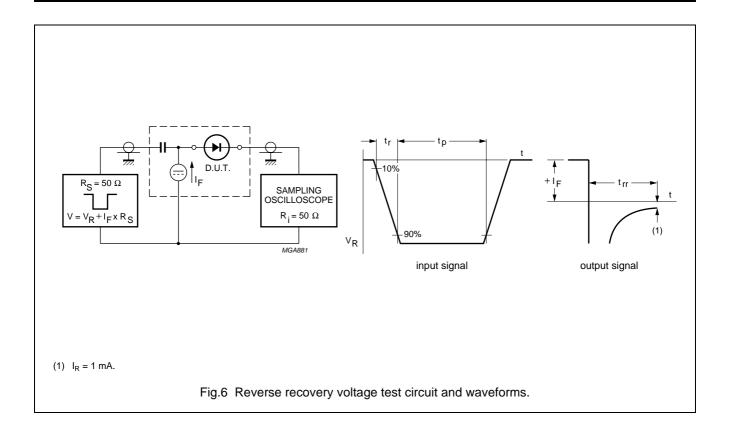
Fig.5 Diode capacitance as a function of reverse voltage; typical values.

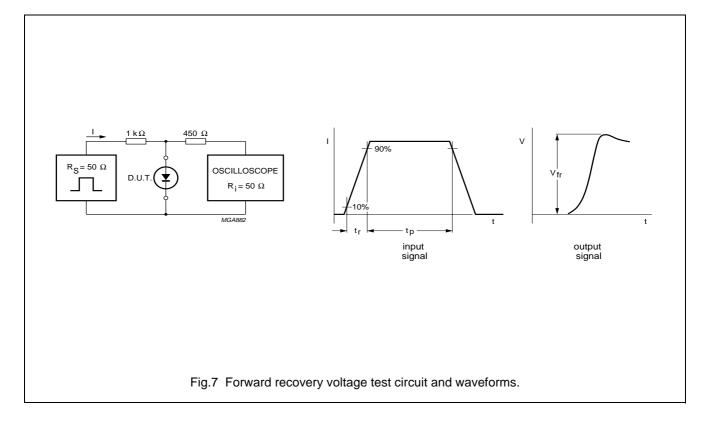
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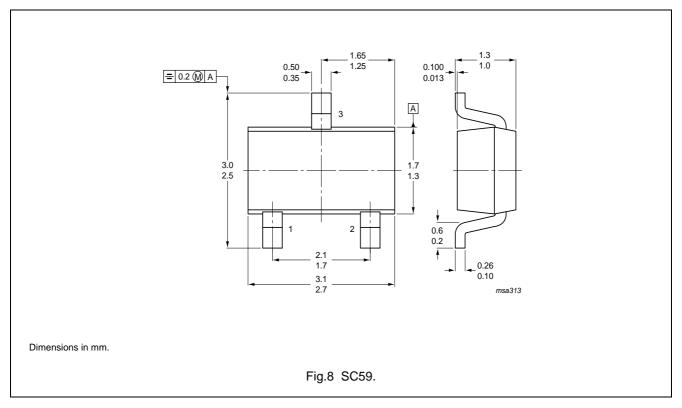


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#### **PACKAGE OUTLINE**



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### High-speed double diode

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#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **NXP Semiconductors**

#### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

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